

Title (en)

Method of forming ferrite thin film and ferrite thin film obtained using the same

Title (de)

Verfahren zur Bildung einer Ferritdünnschicht und dadurch erhaltene Ferritdünnschicht

Title (fr)

Procédé de formation de film mince de ferrite et couche mince de ferrite obtenue à l'aide de celui-ci

Publication

EP 2645383 A2 20131002 (EN)

Application

EP 13160995 A 20130326

Priority

JP 2012076987 A 20120329

Abstract (en)

[Task] To provide a method of forming a ferrite thin film in which it is possible to manufacture a thick film having a film thickness of 1 μm or more using a sol-gel method without causing cracking. [Means for Resolution] A method of forming a ferrite thin film by carrying out a process for forming a coated film by coating a ferrite thin film-forming composition on a heat-resistant substrate and a process for calcining the coated film once or a plurality of times so that the thickness of the calcined film on the substrate becomes a desired thickness, and firing the calcined film formed on the substrate, in which the conditions for firing the calcined film formed on the substrate are under the atmosphere or an oxygen gas or inert gas atmosphere, a temperature-rise rate of 1 °C/minute to 50 °C/minute, a holding temperature of 500 °C to 800 °C, and a holding time of 30 minutes to 120 minutes.

IPC 8 full level

H01F 10/20 (2006.01); **H01F 41/24** (2006.01)

CPC (source: EP KR US)

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